

PHOTOCONDUCTIVE
CdS CELL
VT935G

MAY 20 1994

FEATURES

- Low cost
- Exceptional temperature stability
- Fast response time
- Excellent chopping capability

PRODUCT DESCRIPTION

This photocell consists of a thin film of photoconductive material on a ceramic substrate. A unique method of lead wire attachment provides metallurgical bonding of the wire to the electrode and rigid anchoring of the lead in the ceramic, thus eliminating the need for conductive pastes. A thin plastic coating provides protection for the active surface.

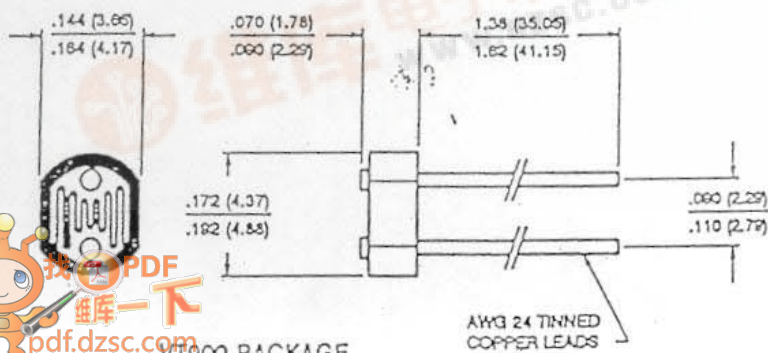
ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNITS
CONTINUOUS POWER DISSIPATION DERATE ABOVE 25° C	P _D	80 1.0	mW mW/°C
MAXIMUM VOLTAGE	V _{MAX}	100	V, PEAK
TEMPERATURE RANGE, OPERATING AND STORAGE	T _A	- 50 to +75	°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25° C (16 HRS. LIGHT ADAPT, MIN.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
RESISTANCE @ 10 lux, 2850 K GROUP A GROUP B GROUP C	R _L	10 20 31		27 38 50	kΩ
DARK RESISTANCE (10 sec. after removal of 10 lux)	R _D	1.0			MΩ
SENSITIVITY $\frac{\text{LOG}(R_{10}/R_{100})}{\text{LOG}(100/10)}$	γ		0.9		
PEAK SPECTRAL RESPONSE (TYPE 3)	λ _P		550		nm

PACKAGE DIMENSIONS inch (mm)



Typical Resistance vs. Illumination Characteristics

